

# AP4527GN3

**Preliminary**

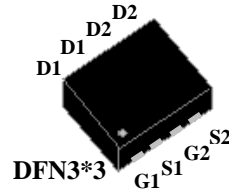


**Advanced Power  
Electronics Corp.**

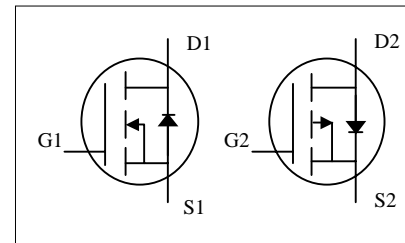
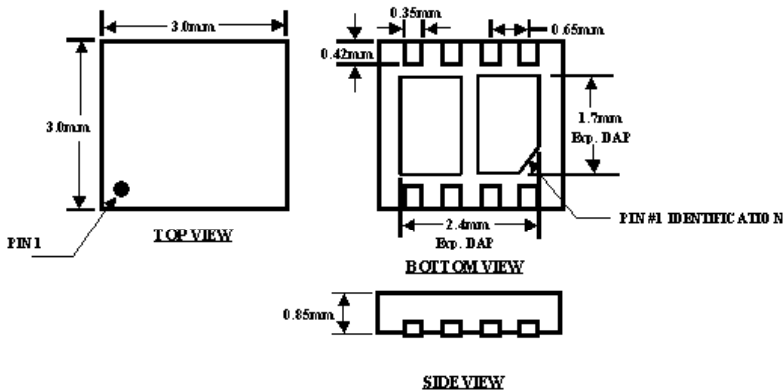
*N AND P-CHANNEL ENHANCEMENT*

*MODE POWER MOSFET*

- ▼ Bottom Exposed DFN
- ▼ Low On-resistance
- ▼ Lower Profile
- ▼ RoHS Compliant



N-CH	$BV_{DSS}$	20V
	$R_{DS(ON)}$	35m $\Omega$
	$I_D$	4.7A
P-CH	$BV_{DSS}$	-20V
	$R_{DS(ON)}$	65m $\Omega$
	$I_D$	-3.3A



## Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
$V_{DS}$	Drain-Source Voltage	20	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current <sup>3</sup>	4.7	-3.3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current <sup>3</sup>	3.8	-2.7	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	20	-20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	1.25		W
	Linear Derating Factor	0.01		W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 100	$^\circ C/W$



**N-CH Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.1	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A	-	-	35	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2A	-	-	52	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.3	-	1.2	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =3.5A	-	3.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±12V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =3.5A	-	9.5	15	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =16V	-	1.2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	4	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =10V	-	8	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	10	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	17	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =10Ω	-	6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	600	960	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V	-	140	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	110	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.2A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V,	-	20	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	14	-	nC



**P-CH Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	-	-0.1	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.5A	-	-	65	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.5A	-	-	100	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.3	-	-1.2	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-2.5A	-	2.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V	-	-	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±12V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =-2.5A	-	10.7	17	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-16V	-	1.8	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	4.7	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =-10V	-	9	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-1A	-	8	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =-10V	-	32	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =10Ω	-	10	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	740	1180	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V	-	170	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	130	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-1.2A, V <sub>GS</sub> =0V	-	-	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =-2.5A, V <sub>GS</sub> =0V,	-	28	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	19	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted FR4 board, t ≤5s.

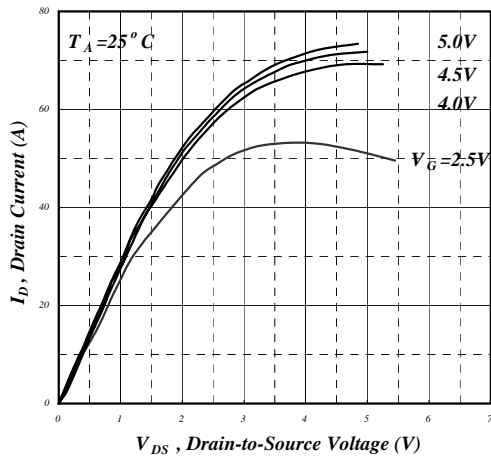


Fig 1. Typical Output Characteristics

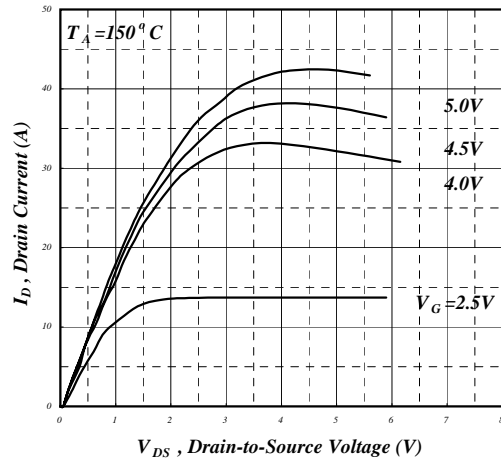


Fig 2. Typical Output Characteristics

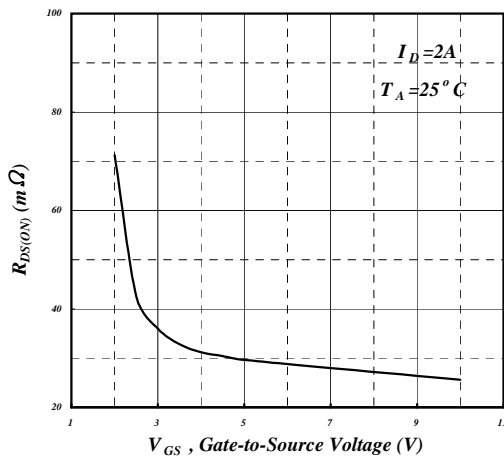


Fig 3. On-Resistance v.s. Gate Voltage

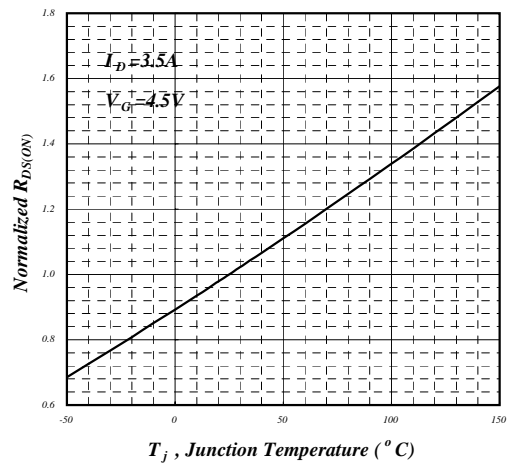


Fig 4. Normalized On-Resistance v.s. Junction Temperature

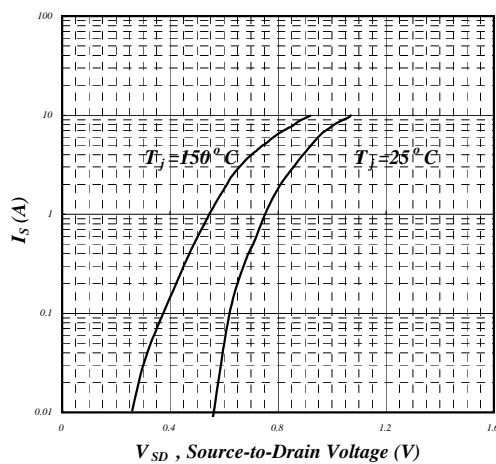


Fig 5. Forward Characteristic of Reverse Diode

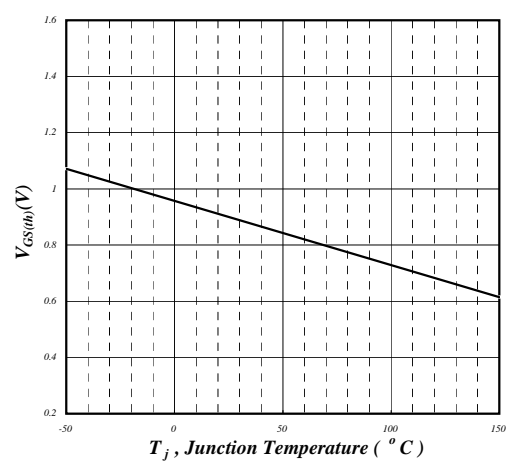


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

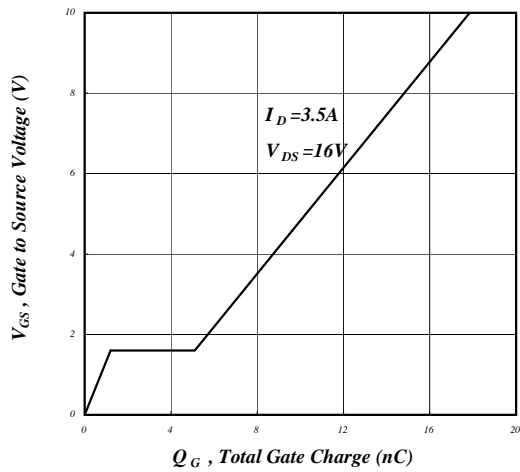


Fig 7. Gate Charge Characteristics

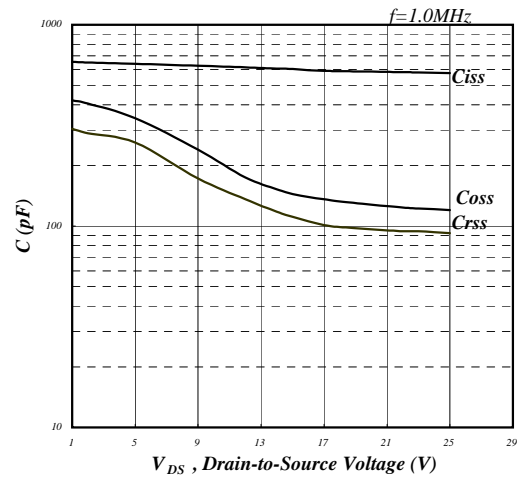


Fig 8. Typical Capacitance Characteristics

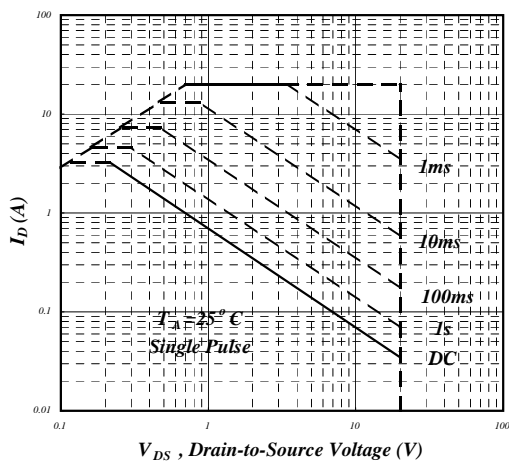


Fig 9. Maximum Safe Operating Area

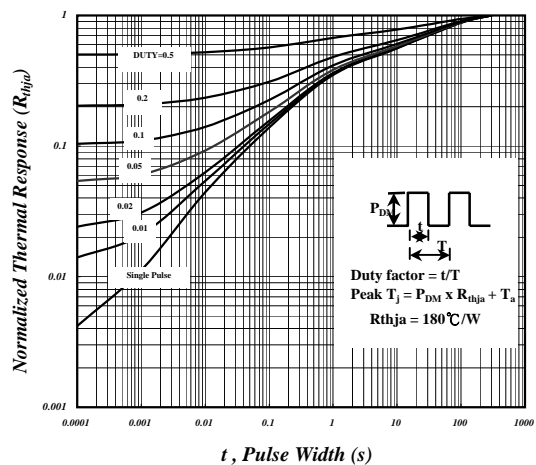


Fig 10. Effective Transient Thermal Impedance

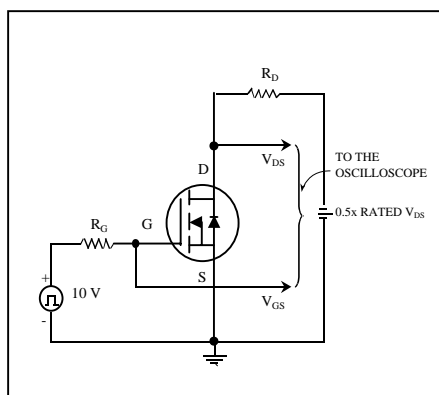


Fig 11. Switching Time Circuit

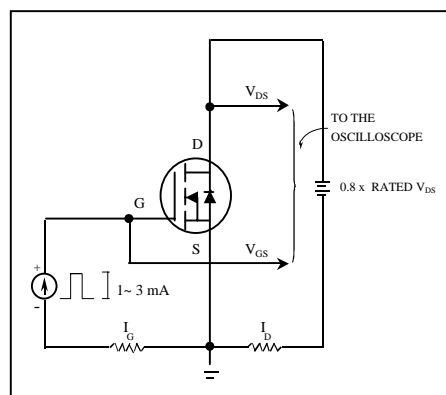


Fig 12. Gate Charge Circuit

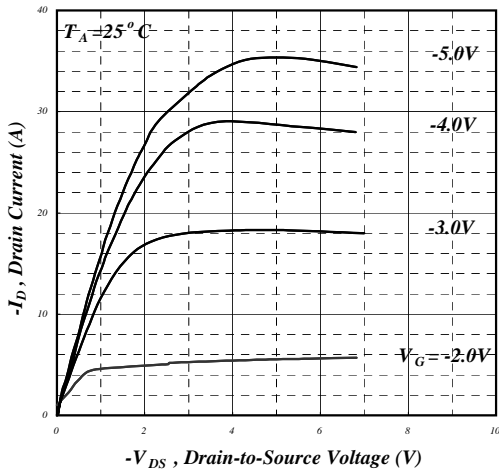


Fig 1. Typical Output Characteristics

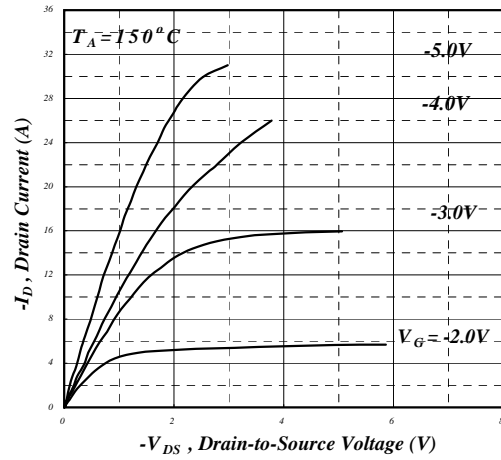


Fig 2. Typical Output Characteristics

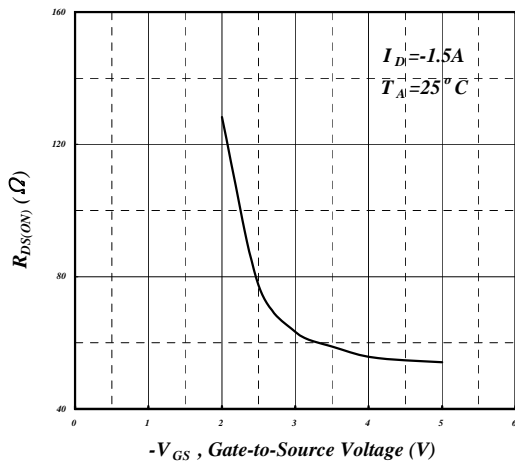


Fig 3. On-Resistance v.s. Gate Voltage

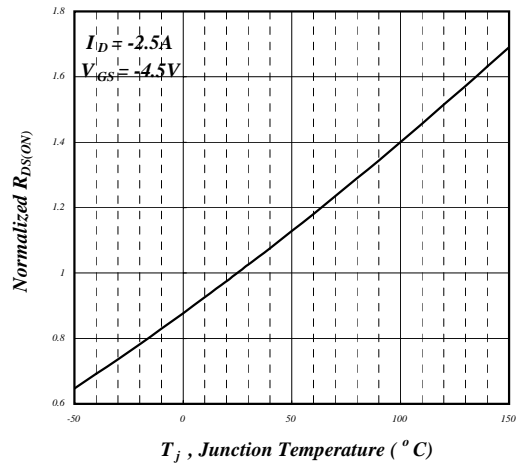


Fig 4. Normalized On-Resistance v.s. Junction Temperature

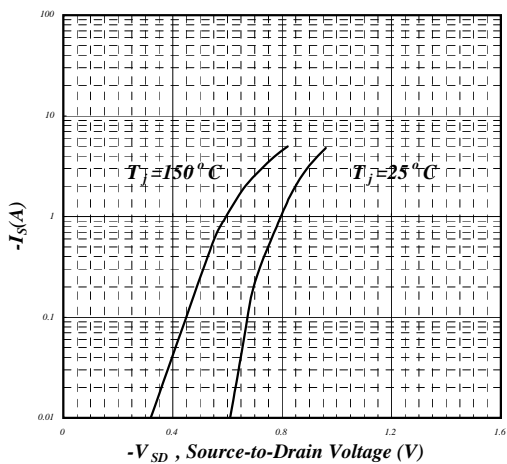


Fig 5. Forward Characteristic of Reverse Diode

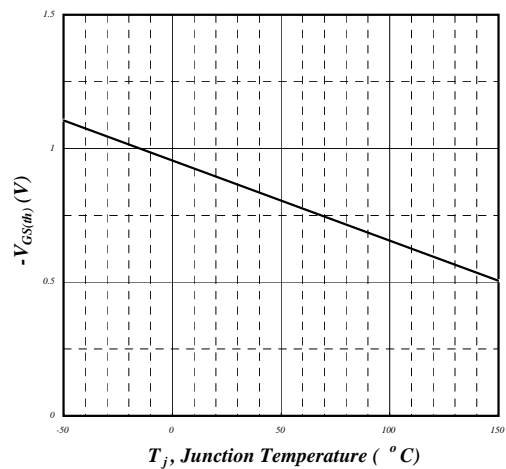


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

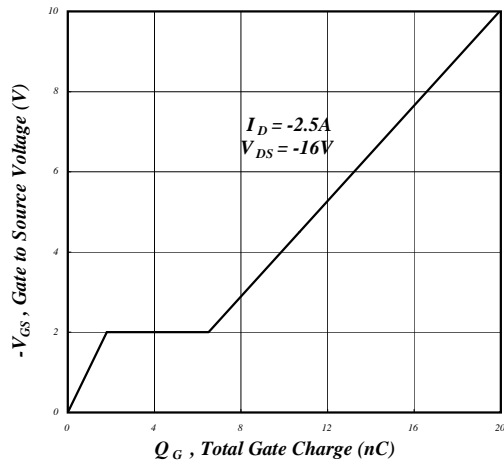


Fig 7. Gate Charge Characteristics

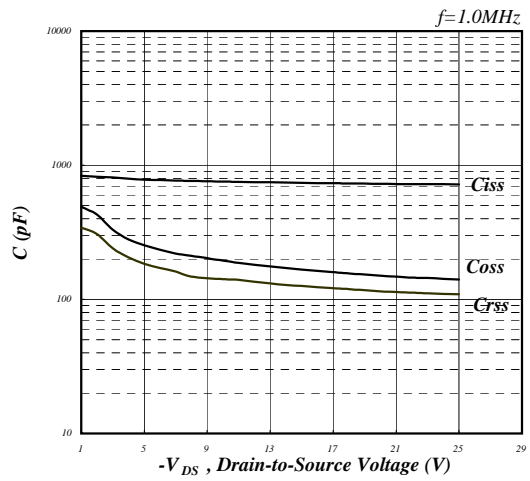


Fig 8. Typical Capacitance Characteristics

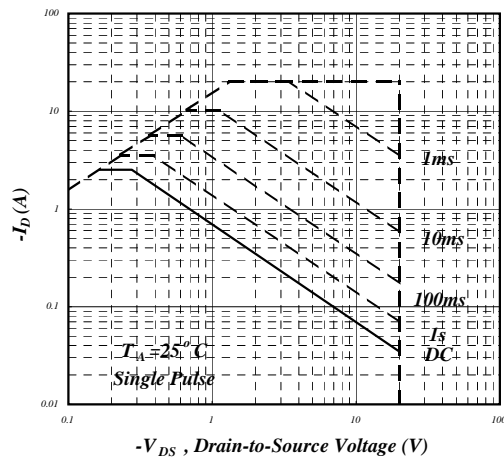


Fig 9. Maximum Safe Operating Area

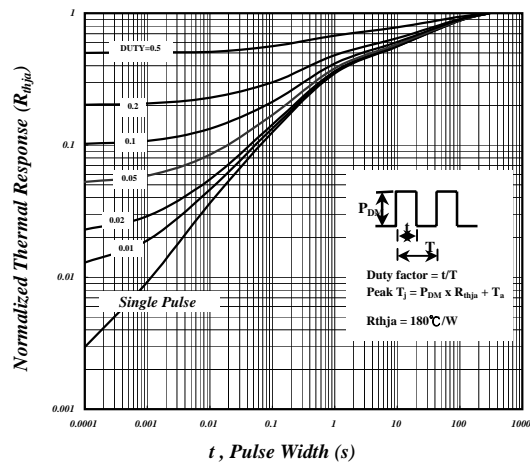


Fig 10. Effective Transient Thermal Impedance

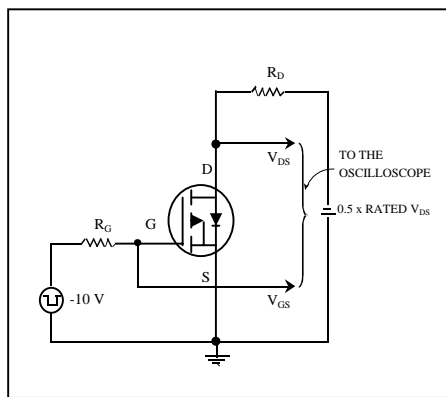


Fig 11. Switching Time Circuit

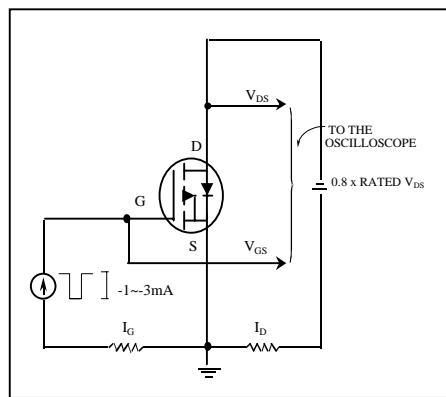


Fig 12. Gate Charge Circuit